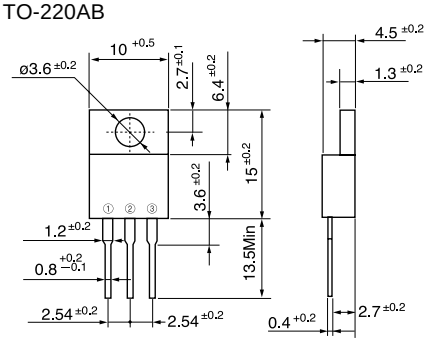
2SC3317

FUJI POWER TRANSISTOR

TRIPLE DIFFUSED PLANER TYPE
HIGH VOLTAGE,HIGH SPEED SWITCHING

■ Outline Drawings

TO-220AB



1 : Base
2 : Collector
3 : Emitter

JEDEC	TO-220AB
EIAJ	SC-46

■ Features

- **High voltage,High speed switching**
- **High reliability**

■ Applications

- **Switching regulators**
- **Ultrasonic generators**
- **High frequency inverters**
- **General purpose power amplifiers**

■ Maximum ratings and characteristics

● **Absolute maximum ratings (Tc=25°C unless otherwise specified)**

Item	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	500	V
Collector-Emitter voltage	V_{CEO}	400	V
Collector-Emitter voltage	$V_{CEO(SUS)}$	400	V
Emitter-Base voltage	V_{EBO}	7	V
Collector current	I_C	5	A
Base current	I_B	2	A
Collector power disspation	P_C	40	W
Operating junction temperature	T_j	+150	℃
Storage temperature	T_{stg}	-65 to +150	℃

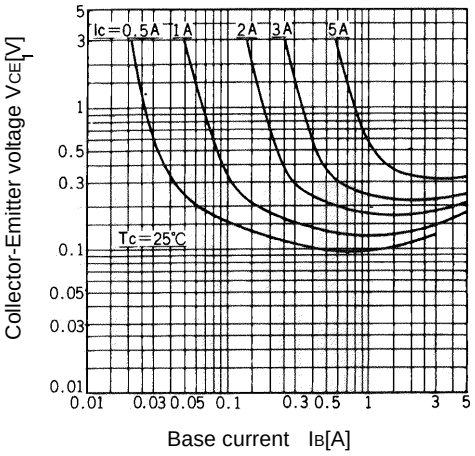
● **Electrical characteristics (T_C =25°C unless otherwise specified)**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Base voltage	V_{CBO}	I_{CBO} = 1mA	500			V
Collector-Emitter voltage	V_{CEO}	I_{CEO} = 10mA	400			V
Collector-Emitter voltage	$V_{CEO(SUS)}$	I_C = 0.2A	400	-		V
Emitter-Base voltage	V_{EBO}	I_{EBO} = 1mA	7	-		V
Collector-Base leakage current	I_{CBO}	V_{CBO} = 500V		-	1.0	mA
Emitter-Base leakage current	I_{EBO}	V_{EBO} = 7V		-	1.0	mA
D.C. current gain	h_{FE}	I_C = 2A, V_{CE} = 5V	10			
Collector-Emitter saturation voltage	$V_{CE(Sat)}$	I_C = 2A, I_B = 0.4A			1.0	V
Base-Emitter saturation voltage	$V_{BE(Sat)}$				1.5	V
*1	t_{on}	I_C = 2.5A, I_{B1} = 0.5A			0.5	µs
Switching time	t_{stg}	I_{B2} = -1A, R_L = 60 ohm			1.5	µs
	t_f	Pw = 20µs Duty=<2%			0.15	µs

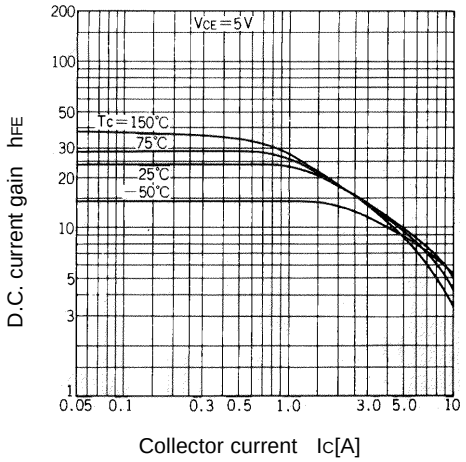
● **Thermal characteristics**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(j-c)}$	Junction to case			3.13	°C/W

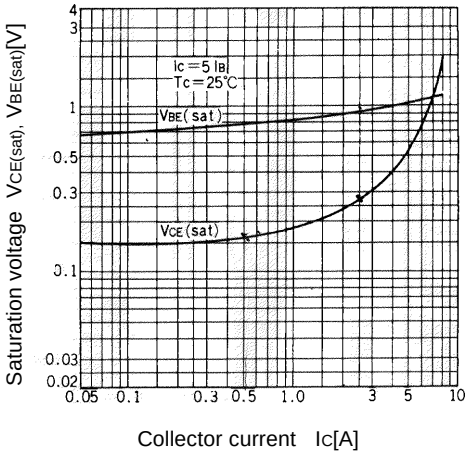
Characteristics



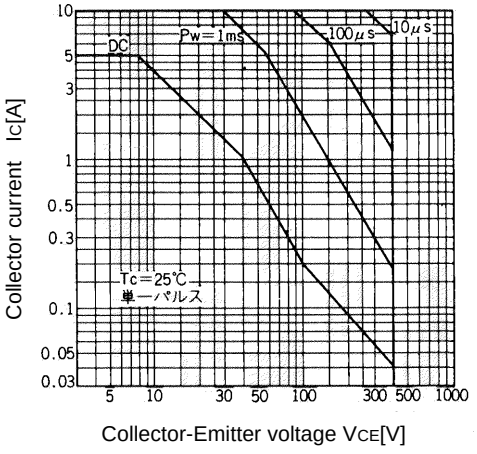
Collector Output Characteristics



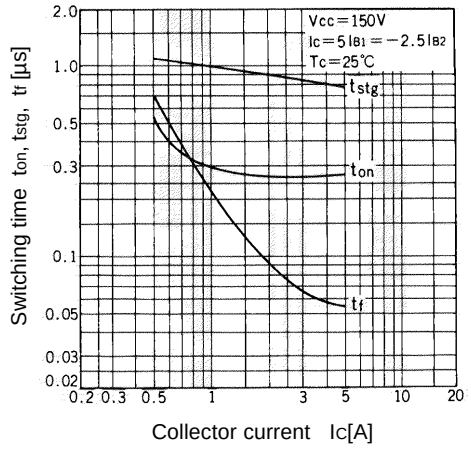
DC Current Gain



Base and Collector Saturation Voltage



Safe Operating Area



Switching Time

***1 Switching Time Test Circuit**